





#### **NPN RF TRANSISTOR IN SOT323**

### **Features**

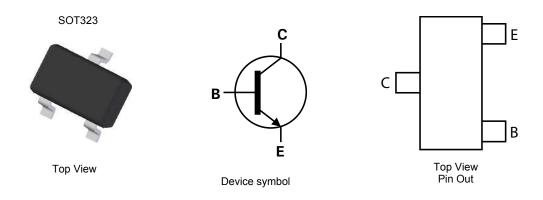
- 3.2GHz unity gain for RF switching applications
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Applications**

RF Switch

### **Mechanical Data**

- Case: SOT323
- Case Material: molded plastic, "Green" molding compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (approximate)



### Ordering Information (Note 4)

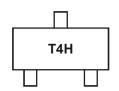
Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZUMTS17NTA	T4H	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

  3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



T4H = Product Type Marking Code





### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	11	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Continuous Collector Current	Ic	50	mA

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Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	Pn	310	mW	
Power Dissipation	(Note 6)	FD	350		
Thermal Resistance, Junction to Ambient	(Note 5)	Б	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	-C/VV	
Thermal Resistance, Junction to Leads (Note 7)		R <sub>0JL</sub>	350	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	100	V	Α

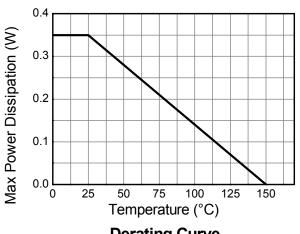
Notes:

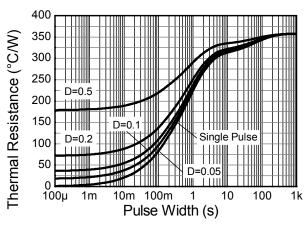
- 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition;
- 6. Same as Note 6, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB
- 7. Thermal resistance from junction to solder-point (at the end of the leads). 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





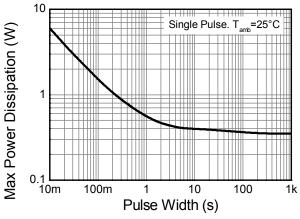
## **Thermal Characteristics and Derating information**





**Derating Curve** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 





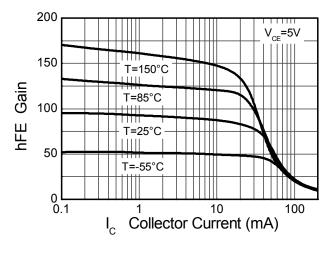
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

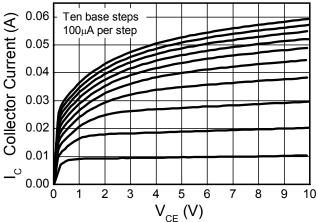
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	20			V	$I_C = 10\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	11	_	_	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	3			V	$I_E = 10\mu A$
Collector Cutoff Current	I <sub>CBO</sub>	_	_	0.5	μΑ	V <sub>CE</sub> = 10V
Emitter Cutoff Current	I <sub>EBO</sub>	_		0.5	μΑ	V <sub>EB</sub> = 2V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	56		180	_	I <sub>C</sub> = 5mA, V <sub>CE</sub> = 10V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(SAT)</sub>	_	_	0.5	V	$I_C = 10mA$ , $I_B = 5mA$
Transition Frequency (Note 9)	f <sub>T</sub>	1.4	3.2		GHz	$V_{CE}$ = 5V, $I_E$ = 25mA, f = 500MHz
Collector Output Capacitance (Note 9)	$C_{ob}$		8.0	1.5	pF	V <sub>CB</sub> = 10V, f = 1.0MHz

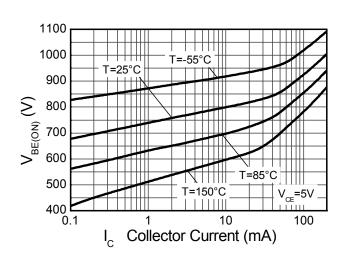
Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%

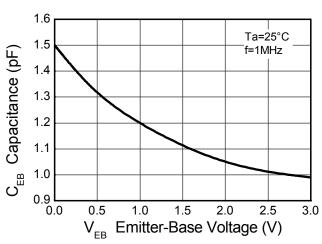


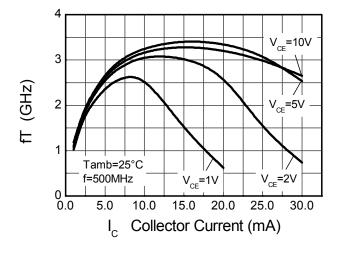
### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

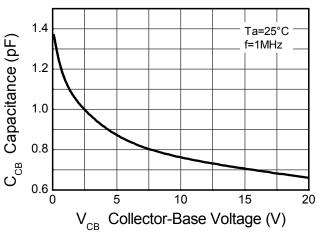








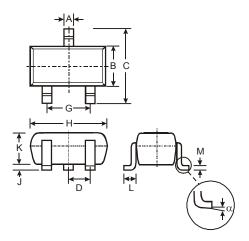






## **Package Outline Dimensions**

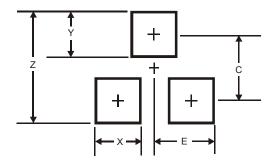
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT323					
Dim	Min	Max	Тур		
Α	0.25	0.40	0.30		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	-	-	0.65		
G	1.20	1.40	1.30		
Η	1.80	2.20	2.15		
J	0.0	0.10	0.05		
K	0.90	1.00	1.00		
L	0.25	0.40	0.30		
М	0.10	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.8			
Х	0.7			
Υ	0.9			
С	1.9			
E	1.0			





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